1. General description

Logic level N-channel MOSFET in an LFPAK33 (Power33) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- · Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with V_{GS(th)} rating of greater than 0.5 V at 175 °C

3. Applications

- 12 V automotive systems
- · Motors, lamps and solenoid control
- Transmission control
- · Ultra high performance power switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	-	60	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>	-	-	22	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	-	44	W
Static charac	teristics					<u>.</u>
R _{DSon}	drain-source on-state resistance	$V_{GS} = 5 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C}; Fig. 11$	-	34	42	mΩ
Dynamic cha	racteristics			•		
Q_{GD}	gate-drain charge	I _D = 5 A; V _{DS} = 48 V; V _{GS} = 5 V; T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	3.4	-	nC



N-channel 60 V, 42 m Ω logic level MOSFET in LFPAK33

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	Source		D
2	S	Source		
3	S	Source		$G \longrightarrow G$
4	G	Gate		mbb076 S
mb	D	Mounting base; connected to drain	1 2 3 4 LFPAK33 (SOT1210)	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BUK9M42-60E	LFPAK33	Plastic, single ended surface mounted package (LFPAK33); 8 leads; 0.65 mm pitch	SOT1210			

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK9M42-60E	94260E

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	60	V
V_{DGR}	drain-gate voltage	R_{GS} = 20 k Ω		-	60	V
V_{GS}	gate-source voltage	DC; T _j ≤ 175 °C		-10	12	V
		Pulsed; T _j ≤ 175 °C	[1] [2]	-15	15	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	44	W
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	22	Α
		V _{GS} = 5 V; T _{mb} = 100 °C; <u>Fig. 2</u>		-	15.2	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 °C$; Fig. 3		-	86	А
T _{stg}	storage temperature			-55	175	°C
T _j	junction temperature			-55	175	°C
Source-drai	n diode		,			
I _S	source current	T _{mb} = 25 °C		-	22	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 °C$		-	86	А

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Symbol	Parameter	Conditions		Min	Max	Unit
Avalanche rugg	edness					
E _{DS(AL)S}		$\begin{split} I_D &= 22 \text{ A; } V_{sup} \leq 60 \text{ V; } R_{GS} = 50 \Omega; \\ V_{GS} &= 5 \text{ V; } T_{j(init)} = 25 \text{ °C; } unclamped; \\ \hline Fig. 4 \end{split}$	[3] [4]	-	11.7	mJ

- [1] Accumulated pulse duration up to 50 hours delivers zero defect ppm.
- [2] Significantly longer life times are achieved by lowering T_i and or V_{GS}
- [3] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [4] Refer to application note AN10273 for further information.

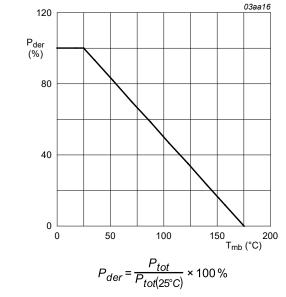


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

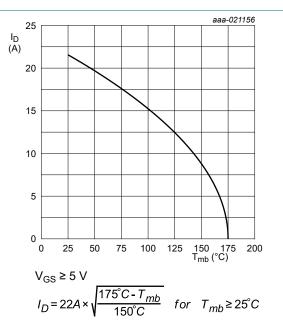


Fig. 2. Continuous drain current as a function of mounting base temperature

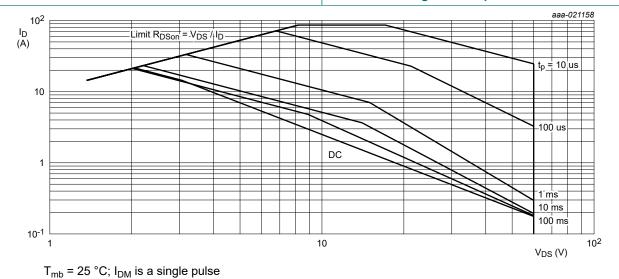
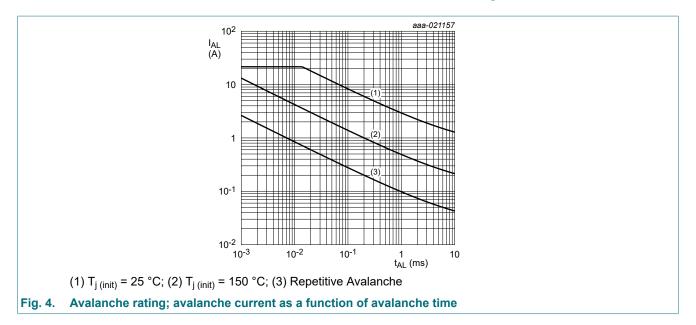


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

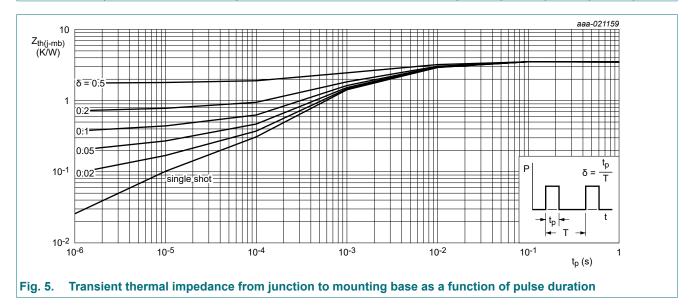
N-channel 60 V, 42 m Ω logic level MOSFET in LFPAK33



9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	2.77	3.4	K/W



10. Characteristics

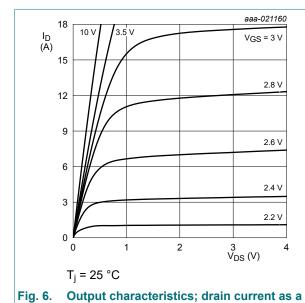
Table 7. Characteristics

Table 11 ellaractorione								
Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Static chara	cteristics		·					
V _{(BR)DSS}	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$		60	-	-	V	
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$		54	-	-	V	

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}; Fig. 9;$ Fig. 10	1.4	1.7	2.1	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = -55 °C; Fig. 10	-	-	2.45	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 10	0.5	-	-	V
I _{DSS}	drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C	-	0.01	1	μΑ
		V _{DS} = 60 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μΑ
I _{GSS}	gate-source threshold voltage drain leakage current gate leakage current drain-source on-state resistance total gate charge gate-source charge gate-drain charge input capacitance output capacitance reverse transfer capacitance turn-on delay time rise time turn-off delay time fall time	V _{GS} = 12 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 5 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 11</u>	-	34	42	mΩ
	resistance	V _{GS} = 10 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 11</u>	-	30	37	mΩ
		V _{GS} = 5 V; I _D = 5 A; T _j = 175 °C; <u>Fig. 12</u>	-	-	95	mΩ
Dynamic ch	naracteristics					
Q _{G(tot)}	total gate charge	I _D = 5 A; V _{DS} = 48 V; V _{GS} = 5 V; T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	8.3	-	nC
Q _{GS}	gate-source charge		-	1.7	-	nC
Q _{GD}	gate-drain charge		-	3.4	-	nC
C _{iss}	input capacitance	T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u> V _{DS} = 25 V; V _{GS} = 0 V; f = 1 MHz;	-	652	867	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>	-	75	90	pF
C _{rss}			-	47	64	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 45 \text{ V}; R_L = 5 \Omega; V_{GS} = 5 \text{ V};$	-	6.2	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 °C$	-	9.7	-	ns
t _{d(off)}	turn-off delay time		-	12.9	-	ns
t _f	fall time		-	8.4	-	ns
Source-drai	in diode		•			
V _{SD}	source-drain voltage	I _S = 5 A; V _{GS} = 0 V; T _j = 25 °C; <u>Fig. 16</u>	-	0.82	1.2	V
t _{rr}	reverse recovery time	$I_S = 5 \text{ A}; \text{ d}I_S/\text{d}t = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	15.6	-	ns
Q _r	recovered charge	V _{DS} = 25 V; T _j = 25 °C	-	11.4	-	nC
	1	1				



function of drain-source voltage; typical values

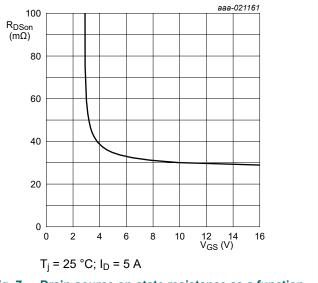


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

N-channel 60 V, 42 mΩ logic level MOSFET in LFPAK33

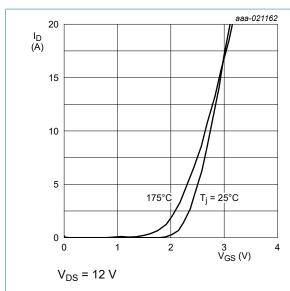


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

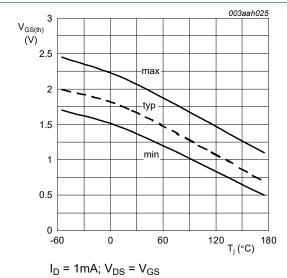


Fig. 10. Gate-source threshold voltage as a function of junction temperature

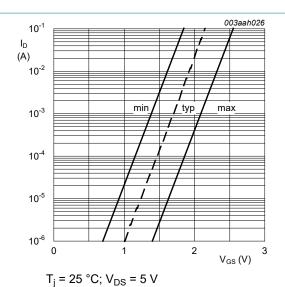


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

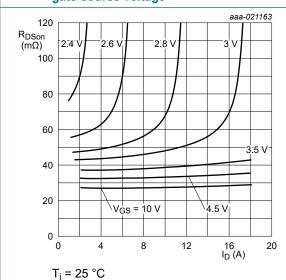


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

N-channel 60 V, 42 mΩ logic level MOSFET in LFPAK33

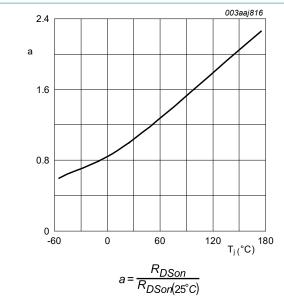


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

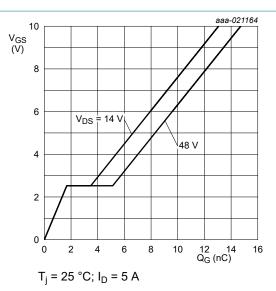


Fig. 13. Gate-source voltage as a function of gate charge; typical values

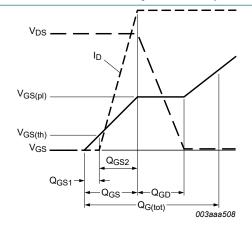
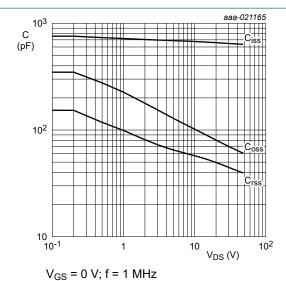
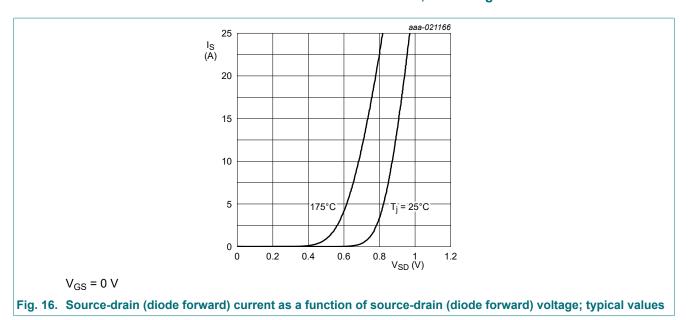


Fig. 14. Gate charge waveform definitions



N-channel 60 V, 42 m Ω logic level MOSFET in LFPAK33



11. Application information

For guidance on how to use and understand this datasheet, please refer to application note <u>AN11158</u> "Understanding power MOSFET datasheet parameters".

N-channel 60 V, 42 mΩ logic level MOSFET in LFPAK33

12. Package outline

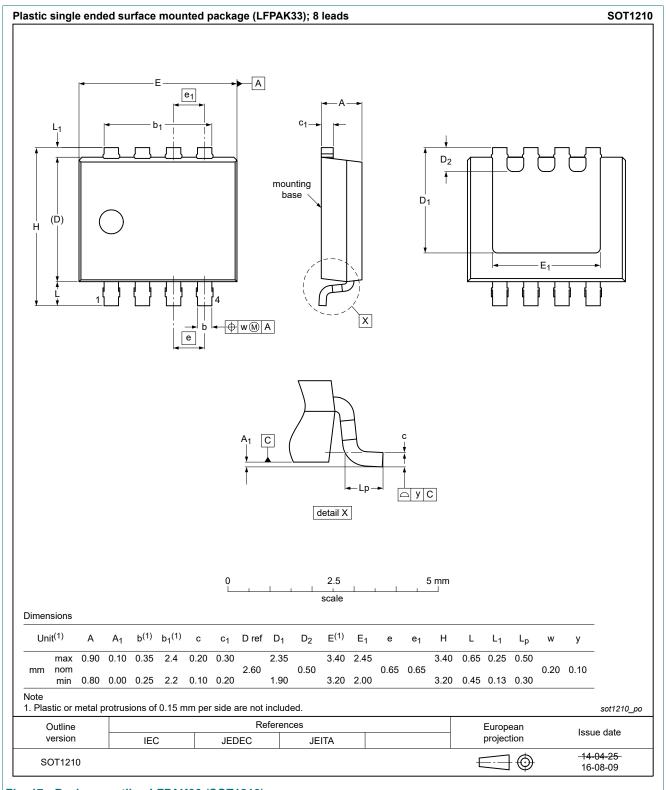
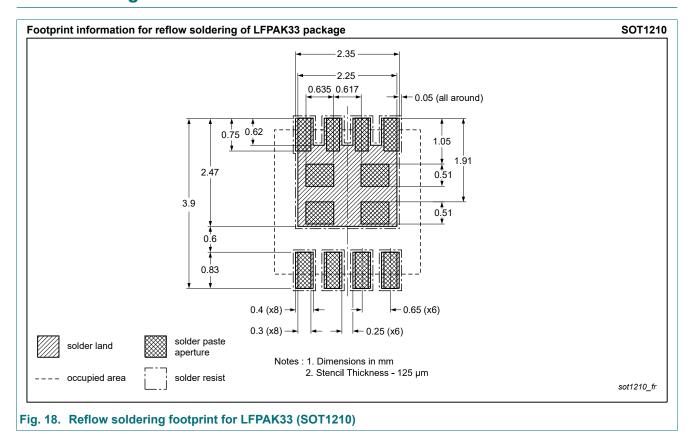


Fig. 17. Package outline LFPAK33 (SOT1210)

N-channel 60 V, 42 m Ω logic level MOSFET in LFPAK33

13. Soldering



N-channel 60 V, 42 mΩ logic level MOSFET in LFPAK33

14. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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BUK9M42-60E

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